

CD54HC243, CD74HC243, CD54HCT243, CD74HCT243

High-Speed CMOS Logic Quad-Bus Transceiver with Three-State Outputs

Features

- Typical Propagation Delay (A to B, B to A) of 7ns at $V_{CC} = 5V$, $C_L = 15pF$, $T_A = 25^\circ C$
- Three-State Outputs
- Buffered Inputs
- Fanout (Over Temperature Range)
 - Standard Outputs 10 LSTTL Loads
 - Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range . . . $-55^\circ C$ to $125^\circ C$
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- HC Types
 - 2V to 6V Operation
 - High Noise Immunity: $N_{IL} = 30\%$, $N_{IH} = 30\%$ of V_{CC} at $V_{CC} = 5V$
- HCT Types
 - 4.5V to 5.5V Operation
 - Direct LSTTL Input Logic Compatibility, $V_{IL} = 0.8V$ (Max), $V_{IH} = 2V$ (Min)
 - CMOS Input Compatibility, $I_I \leq 1\mu A$ at V_{OL} , V_{OH}

Description

The 'HC243 and 'HCT243 silicon-gate CMOS three-state bidirectional noninverting buffers are intended for two-way asynchronous communication between data buses. They have high-drive-current outputs that enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits and have speeds comparable to low-power Schottky TTL circuits. They can drive 15 LSTTL loads.

The states of the output-enable (\overline{OEB} , OEA) inputs determine both the direction of flow (A to B, B to A), and the three-state mode.

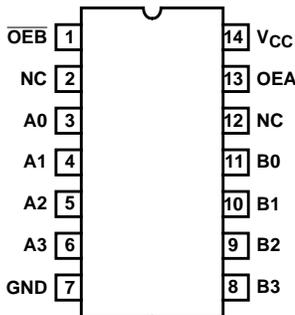
Ordering Information

PART NUMBER	TEMP. RANGE (°C)	PACKAGE
CD54HC243F3A	-55 to 125	14 Ld CERDIP
CD54HCT243F3A	-55 to 125	14 Ld CERDIP
CD74HC243E	-55 to 125	14 Ld PDIP
CD74HC243M	-55 to 125	14 Ld SOIC
CD74HC243MT	-55 to 125	14 Ld SOIC
CD74HC243M96	-55 to 125	14 Ld SOIC
CD74HCT243E	-55 to 125	14 Ld PDIP
CD74HCT243M	-55 to 125	14 Ld SOIC

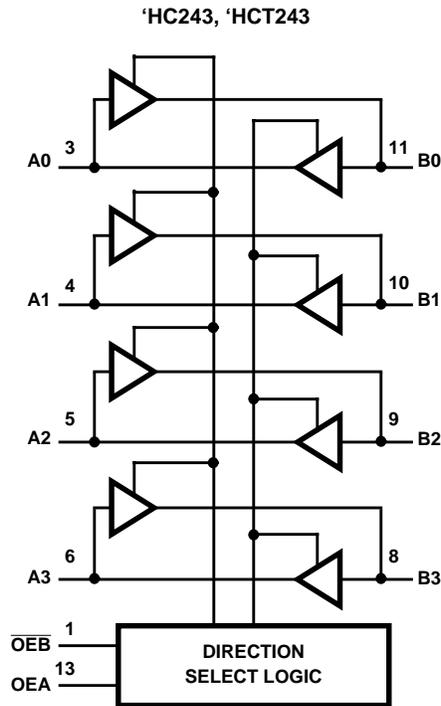
NOTE: When ordering, use the entire part number. The suffix 96 denotes tape and reel. The suffix T denotes a small-quantity reel of 250.

Pinout

CD54HC243, CD54HCT243
(CERDIP)
CD74HC243, CD74HCT243
(PDIP, SOIC)
TOP VIEW



Functional Diagram



TRUTH TABLE

CONTROL INPUTS		HC, HCT243 SERIES	
		DATA PORT STATUS	
$\overline{\text{OEB}}$	OEA	An	Bn
H	H	O	I
L	H	Z	Z
H	L	Z	Z
L	L	I	O

H= High Voltage Level

L= Low Voltage Level

I= Input

O= Output (Same Level as Input)

Z= High Impedance

To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10kΩ to 1MΩ resistors.

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Absolute Maximum Ratings

DC Supply Voltage, V_{CC}	-0.5V to 7V
DC Input Diode Current, I_{IK}	
For $V_I < -0.5V$ or $V_I > V_{CC} + 0.5V$	$\pm 20mA$
DC Output Diode Current, I_{OK}	
For $V_O < -0.5V$ or $V_O > V_{CC} + 0.5V$	$\pm 20mA$
DC Drain Current, per Output, I_O	
For $-0.5V < V_O < V_{CC} + 0.5V$	$\pm 35mA$
DC Output Source or Sink Current per Output Pin, I_O	
For $V_O > -0.5V$ or $V_O < V_{CC} + 0.5V$	$\pm 25mA$
DC V_{CC} or Ground Current, I_{CC}	$\pm 70mA$

Thermal Information

Thermal Resistance (Typical, Note 1)	θ_{JA} (°C/W)
E (PDIP) Package	80
M (SOIC) Package	86
Maximum Junction Temperature	150°C
Maximum Storage Temperature Range	-65°C to 150°C
Maximum Lead Temperature (Soldering 10s)	300°C (SOIC - Lead Tips Only)

Operating Conditions

Temperature Range (T_A)	-55°C to 125°C
Supply Voltage Range, V_{CC}	
HC Types2V to 6V
HCT Types	4.5V to 5.5V
DC Input or Output Voltage, V_I, V_O	0V to V_{CC}
Input Rise and Fall Time	
2V	1000ns (Max)
4.5V	500ns (Max)
6V	400ns (Max)

CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.

NOTE:

- The package thermal impedance is calculated in accordance with JESD 51-7.

DC Electrical Specifications

PARAMETER	SYMBOL	TEST CONDITIONS		V_{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V_I (V)	I_O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
HC TYPES												
High Level Input Voltage	V_{IH}	-	-	2	1.5	-	-	1.5	-	1.5	-	V
				4.5	3.15	-	-	3.15	-	3.15	-	V
				6	4.2	-	-	4.2	-	4.2	-	V
Low Level Input Voltage	V_{IL}	-	-	2	-	-	0.5	-	0.5	-	0.5	V
				4.5	-	-	1.35	-	1.35	-	1.35	V
				6	-	-	1.8	-	1.8	-	1.8	V
High Level Output Voltage CMOS Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	2	1.9	-	-	1.9	-	1.9	-	V
			-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads	V_{OH}	V_{IH} or V_{IL}	-0.02	6	5.9	-	-	5.9	-	5.9	-	V
			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	-7.8	6	5.48	-	-	5.34	-	5.2	-	V
			0.02	2	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage CMOS Loads	V_{OL}	V_{IH} or V_{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
			0.02	6	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads	V_{OL}	V_{IH} or V_{IL}	6	4.5	-	-	0.26	-	0.33	-	0.4	V
			7.8	6	-	-	0.26	-	0.33	-	0.4	V

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DC Electrical Specifications (Continued)

PARAMETER	SYMBOL	TEST CONDITIONS		V _{CC} (V)	25°C			-40°C TO 85°C		-55°C TO 125°C		UNITS
		V _I (V)	I _O (mA)		MIN	TYP	MAX	MIN	MAX	MIN	MAX	
Input Leakage Current	I _I	V _{CC} or GND	-	6	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	6	-	-	8	-	80	-	160	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	6	-	-	±0.5	-	±0.5	-	±10	μA
HCT TYPES												
High Level Input Voltage	V _{IH}	-	-	4.5 to 5.5	2	-	-	2	-	2	-	V
Low Level Input Voltage	V _{IL}	-	-	4.5 to 5.5	-	-	0.8	-	0.8	-	0.8	V
High Level Output Voltage CMOS Loads	V _{OH}	V _{IH} or V _{IL}	-0.02	4.5	4.4	-	-	4.4	-	4.4	-	V
High Level Output Voltage TTL Loads			-6	4.5	3.98	-	-	3.84	-	3.7	-	V
Low Level Output Voltage CMOS Loads	V _{OL}	V _{IH} or V _{IL}	0.02	4.5	-	-	0.1	-	0.1	-	0.1	V
Low Level Output Voltage TTL Loads			6	4.5	-	-	0.26	-	0.33	-	0.4	V
Input Leakage Current	I _I	V _{CC} to GND	-	5.5	-	-	±0.1	-	±1	-	±1	μA
Quiescent Device Current	I _{CC}	V _{CC} or GND	0	5.5	-	-	8	-	80	-	160	μA
Additional Quiescent Device Current Per Input Pin: 1 Unit Load	ΔI _{CC} (Note 2)	V _{CC} -2.1	-	4.5 to 5.5	-	100	360	-	450	-	490	μA
Three-State Leakage Current	I _{OZ}	V _{IL} or V _{IH}	-	5.5	-	-	±0.5	-	±5.0	-	±10	μA

NOTE:

- For dual-supply systems theoretical worst case (V_I = 2.4V, V_{CC} = 5.5V) specification is 1.8mA.

HCT Input Loading Table

INPUT	UNIT LOADS
An, Bn	1.1
OEA, \overline{OEB}	0.6

NOTE: Unit Load is ΔI_{CC} limit specified in DC Electrical Specifications table, e.g., 360μA max at 25°C.

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Switching Specifications Input $t_r, t_f = 6\text{ns}$

PARAMETER	SYMBOL	TEST CONDITIONS	V_{CC} (V)	25°C		-40°C TO 85°C	-55°C TO 125°C	UNITS
				TYP	MAX	MAX	MAX	
HC TYPES								
Propagation Delay Data to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	2	-	90	115	135	ns
			4.5	-	18	23	27	ns
		$C_L = 15\text{pF}$	5	7	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	15	20	23	ns
Output High-Z, to High Level to Low Level	t_{PZH}, t_{PZL}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	$C_L = 50\text{pF}$	2	-	150	190	225	ns
		$C_L = 50\text{pF}$	4.5	-	30	38	45	ns
		$C_L = 15\text{pF}$	5	12	-	-	-	ns
		$C_L = 50\text{pF}$	6	-	26	33	38	ns
Output Transition Times	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	2	-	60	75	90	ns
			4.5	-	12	15	18	ns
			6	-	10	13	15	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	80	-	-	-	pF
HCT TYPES								
Propagation Delay Data to Outputs	t_{PLH}, t_{PHL}	$C_L = 50\text{pF}$	4.5	-	22	28	33	ns
		$C_L = 15\text{pF}$	5	9	-	-	-	ns
Output High-Z to High Level to Low Level	t_{PZH}, t_{PZL}	$C_L = 50\text{pF}$	4.5	-	34	43	51	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output High Level, Output Low Level to High-Z	t_{PHZ}, t_{PLZ}	$C_L = 50\text{pF}$	4.5	-	35	44	53	ns
		$C_L = 15\text{pF}$	5	14	-	-	-	ns
Output Transition Times	t_{TLH}, t_{THL}	$C_L = 50\text{pF}$	4.5	-	12	15	18	ns
Input Capacitance	C_I	-	-	-	10	10	10	pF
Three-State Output Capacitance	C_O	-	-	-	20	20	20	pF
Power Dissipation Capacitance (Notes 3, 4)	C_{PD}	-	5	91	-	-	-	pF

NOTES:

- C_{PD} is used to determine the dynamic power consumption, per channel.
- $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = Input Frequency, f_O = Output Frequency, C_L = Output Load Capacitance, V_{CC} = Supply Voltage.

Test Circuits and Waveforms

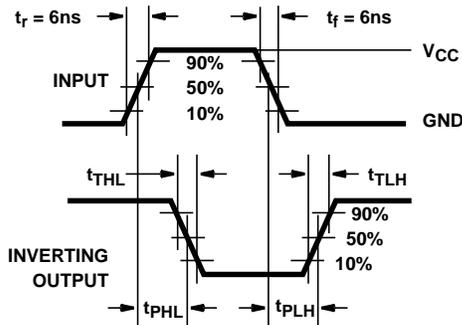


FIGURE 1. HC AND HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

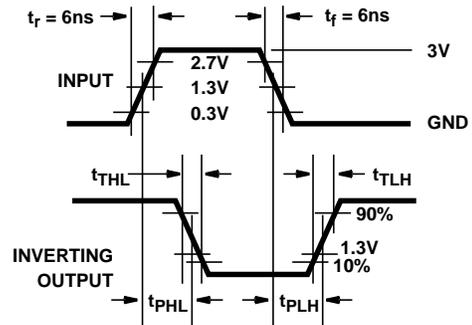


FIGURE 2. HCT TRANSITION TIMES AND PROPAGATION DELAY TIMES, COMBINATION LOGIC

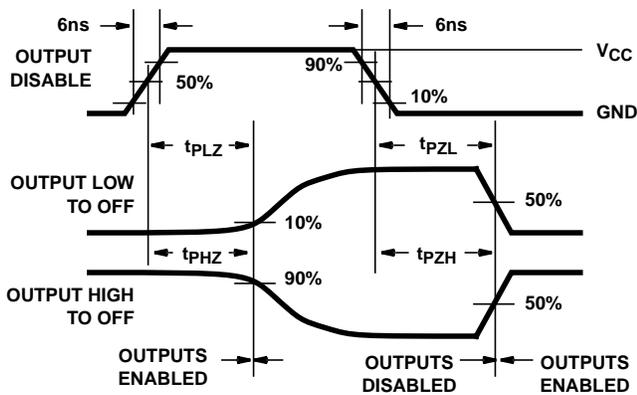


FIGURE 3. HC THREE-STATE PROPAGATION DELAY WAVEFORM

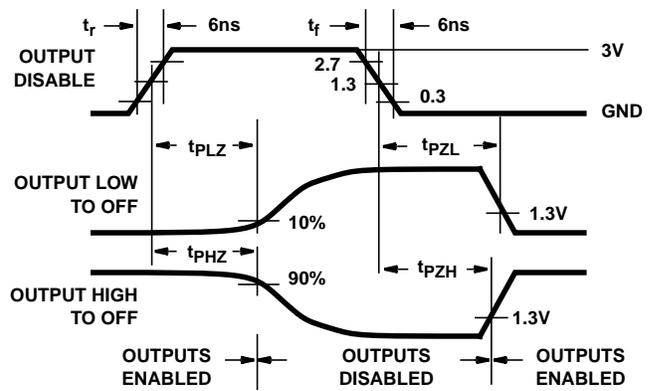
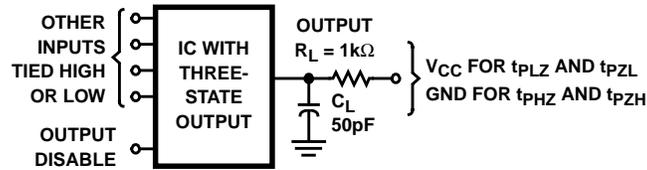


FIGURE 4. HCT THREE-STATE PROPAGATION DELAY WAVEFORM



NOTE: Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L = 1k\Omega$ V_{CC} , $C_L = 50pF$.

FIGURE 5. HC AND HCT THREE-STATE PROPAGATION DELAY TEST CIRCUIT

PACKAGING INFORMATION

Orderable Device	Status ⁽¹⁾	Package Type	Package Drawing	Pins	Package Qty	Eco Plan ⁽²⁾	Lead/Ball Finish	MSL Peak Temp ⁽³⁾
8409001CA	ACTIVE	CDIP	J	14	1	TBD	A42 SNPB	N / A for Pkg Type
CD54HC243F	ACTIVE	CDIP	J	14	1	TBD	A42 SNPB	N / A for Pkg Type
CD54HC243F3A	ACTIVE	CDIP	J	14	1	TBD	A42 SNPB	N / A for Pkg Type
CD54HCT243F3A	ACTIVE	CDIP	J	14	1	TBD	A42 SNPB	N / A for Pkg Type
CD74HC243E	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
CD74HC243EE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
CD74HC243M	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HC243M96	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HC243M96E4	ACTIVE	SOIC	D	14	2500	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HC243ME4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HC243MT	ACTIVE	SOIC	D	14	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HC243MTE4	ACTIVE	SOIC	D	14	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HCT243E	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
CD74HCT243EE4	ACTIVE	PDIP	N	14	25	Pb-Free (RoHS)	CU NIPDAU	N / A for Pkg Type
CD74HCT243M	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM
CD74HCT243ME4	ACTIVE	SOIC	D	14	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

⁽²⁾ Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check <http://www.ti.com/productcontent> for the latest availability information and additional product content details.

TBD: The Pb-Free/Green conversion plan has not been defined.

Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.

Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.

Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

⁽³⁾ MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

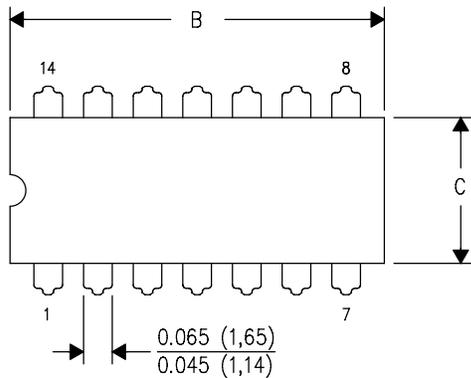
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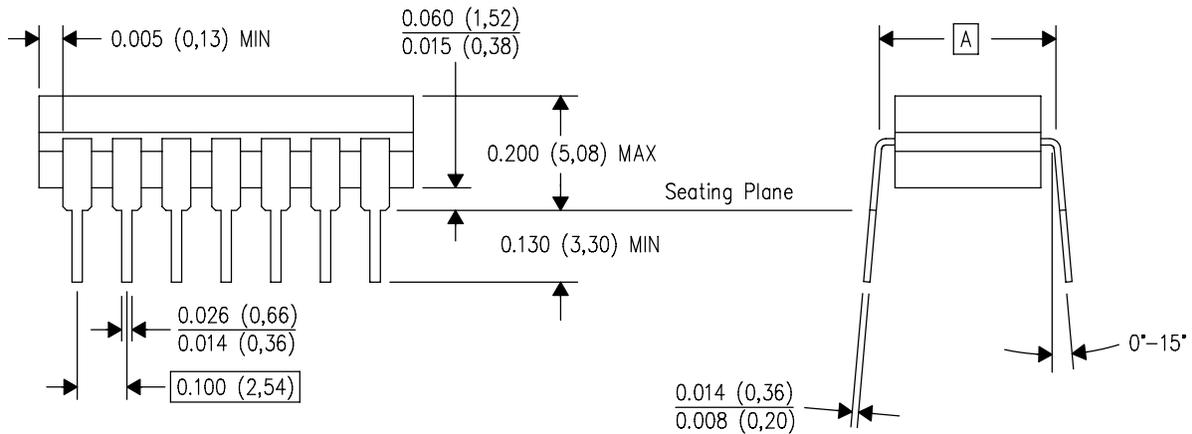
J (R-GDIP-T**)

14 LEADS SHOWN

CERAMIC DUAL IN-LINE PACKAGE



DIM \ PINS **	14	16	18	20
A	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC	0.300 (7,62) BSC
B MAX	0.785 (19,94)	.840 (21,34)	0.960 (24,38)	1.060 (26,92)
B MIN	—	—	—	—
C MAX	0.300 (7,62)	0.300 (7,62)	0.310 (7,87)	0.300 (7,62)
C MIN	0.245 (6,22)	0.245 (6,22)	0.220 (5,59)	0.245 (6,22)

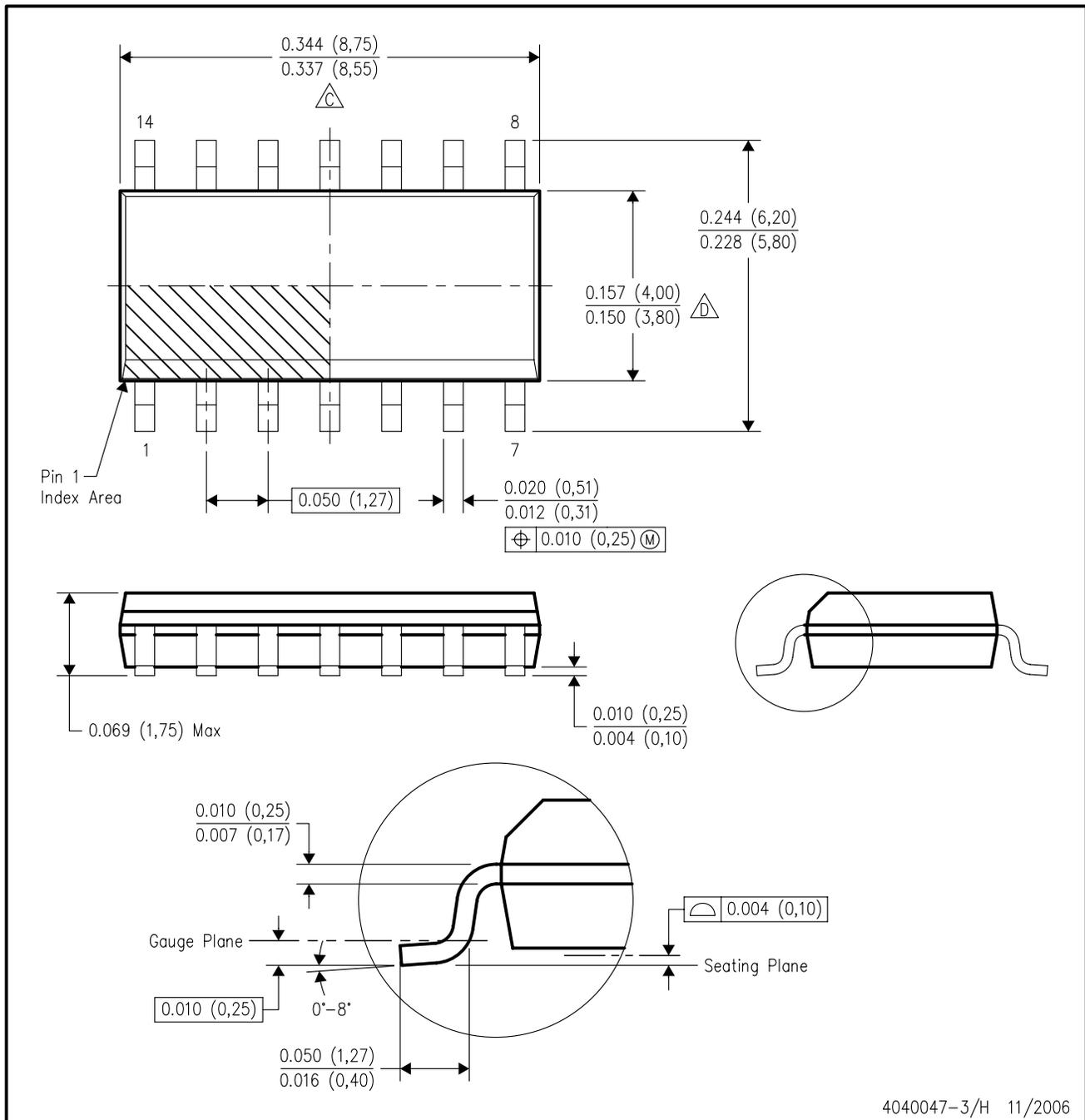


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- NOTES:
- All linear dimensions are in inches (millimeters).
 - This drawing is subject to change without notice.
 - This package is hermetically sealed with a ceramic lid using glass frit.
 - Index point is provided on cap for terminal identification only on press ceramic glass frit seal only.
 - Falls within MIL STD 1835 GDIP1-T14, GDIP1-T16, GDIP1-T18 and GDIP1-T20.

D (R-PDSO-G14)

PLASTIC SMALL-OUTLINE PACKAGE



- NOTES:
- A. All linear dimensions are in inches (millimeters).
 - B. This drawing is subject to change without notice.
 - C. Body length does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 (0,15) per end.
 - D. Body width does not include interlead flash. Interlead flash shall not exceed .017 (0,43) per side.
 - E. Reference JEDEC MS-012 variation AB.

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